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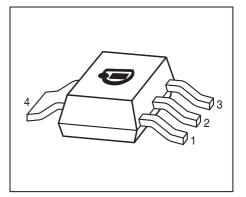


PZTA42

NPN Silicon High-Voltage Transistors

- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary type: PZTA92 (PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101





Туре	Marking	Pin Configuration						Package
PZTA42	PZTA42	1=B	2=C	3=E	4=C	-	-	SOT223

Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V _{CEO}	300	V	
Collector-base voltage	V _{CBO}	300		
Emitter-base voltage	V _{EBO}	6		
Collector current	I _C	500	mA	
Base current	I _B	100		
Total power dissipation-	P _{tot}	1.5	W	
<i>T</i> _S ≤ 124 °C				
Junction temperature	Ti	150	°C	
Storage temperature	T _{stq}	-65 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 17	K/W

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)



Parameter	Symbol	Values			Unit
			typ. max.		
DC Characteristics	• • •		•		•
Collector-emitter breakdown voltage	V _{(BR)CEO}	300	-	-	V
<i>I</i> _C = 1 mA, <i>I</i> _B = 0					
Collector-base breakdown voltage	V _{(BR)CBO}	300	-	-	
<i>I</i> _C = 100 μA, <i>I</i> _E = 0					
Emitter-base breakdown voltage	V _{(BR)EBO}	6	-	-	
<i>I</i> _E = 100 μA, <i>I</i> _C = 0					
Collector-base cutoff current	I _{CBO}				μA
$V_{\rm CB} = 200 \text{ V}, I_{\rm E} = 0$		-	-	0.1	
$V_{\rm CB}$ = 200 V, $I_{\rm E}$ = 0 , $T_{\rm A}$ = 150 °C		-	-	20	
Emitter-base cutoff current	I _{EBO}	-	-	100	nA
$V_{\rm EB}$ = 5 V, $I_{\rm C}$ = 0					
DC current gain ¹⁾	h _{FE}				-
<i>I</i> _C = 1 mA, <i>V</i> _{CE} = 10 V		25	-	-	
<i>I</i> _C = 10 mA, <i>V</i> _{CE} = 10 V		40	-	-	
<i>I</i> _C = 30 mA, <i>V</i> _{CE} = 10 V		40	-	-	
Collector-emitter saturation voltage1)	V _{CEsat}	-	-	0.5	V
<i>I</i> _C = 20 mA, <i>I</i> _B = 2 mA					
Base emitter saturation voltage ¹⁾	V _{BEsat}	-	-	0.9	
<i>I</i> _C = 20 mA, <i>I</i> _B = 2 mA					
AC Characteristics					
Transition frequency	f _T	-	70	-	MHz
$I_{2} = 20 \text{ MHz} $ $V_{2} = -10 \text{ V} f = 20 \text{ MHz}$					

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

$I_{\rm C}$ = 20 MHz, $V_{\rm CE}$ = 10 V, f = 20 MHz				
Collector-base capacitance	C _{cb}	-	-	3
$V_{\rm CB}$ = 20 V, <i>f</i> = 1 MHz				

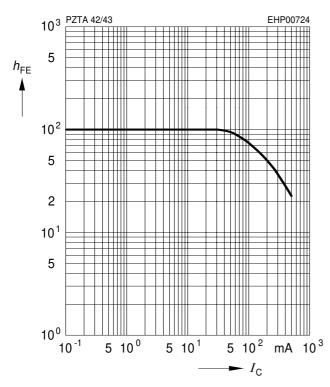
¹Pulse test: t < 300µs; D < 2%

pF

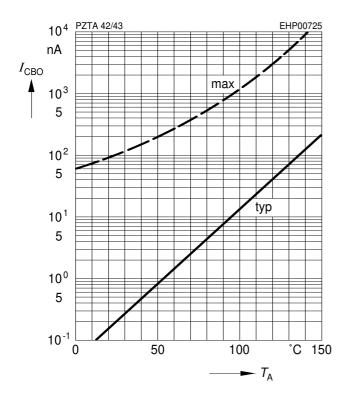


DC current gain $h_{\text{FE}} = f(I_{\text{C}})$

*V*_{CE} = 10 V

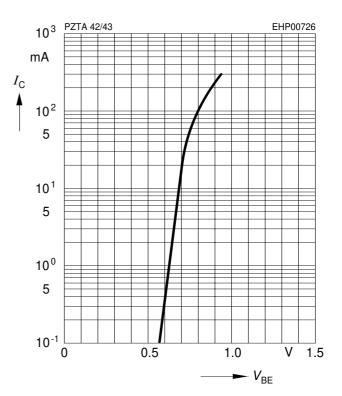


Collector cutoff current $I_{CBO} = f(T_A)$ $V_{CB} = 200 \text{ V}$

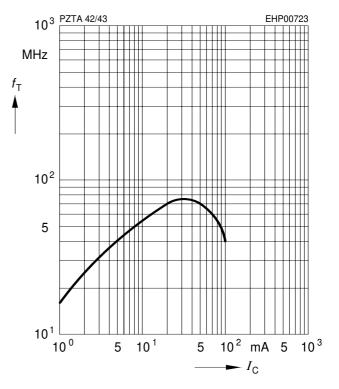


Collector current $I_{\rm C} = f(V_{\rm BE})$

 $V_{CE} = 10V$

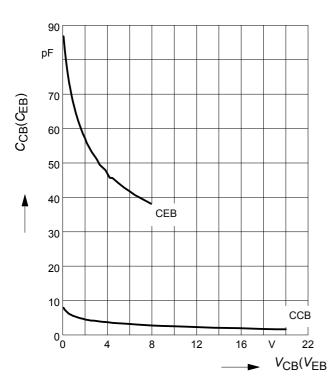


Transition frequency $f_{\rm T} = f(I_{\rm C})$ $V_{\rm CE} = 10 \text{ V}$



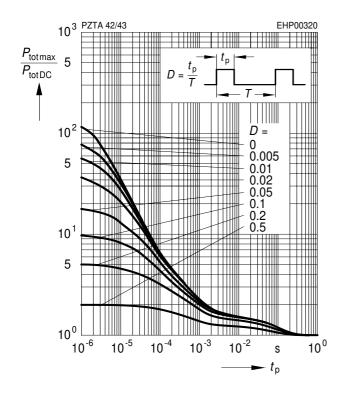


Collector-base capacitance $C_{cb} = f(V_{CB})$ Emitter-base capacitance $C_{eb} = f(V_{EB})$

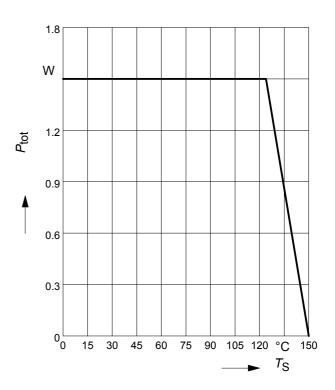


Permissible Pulse Load

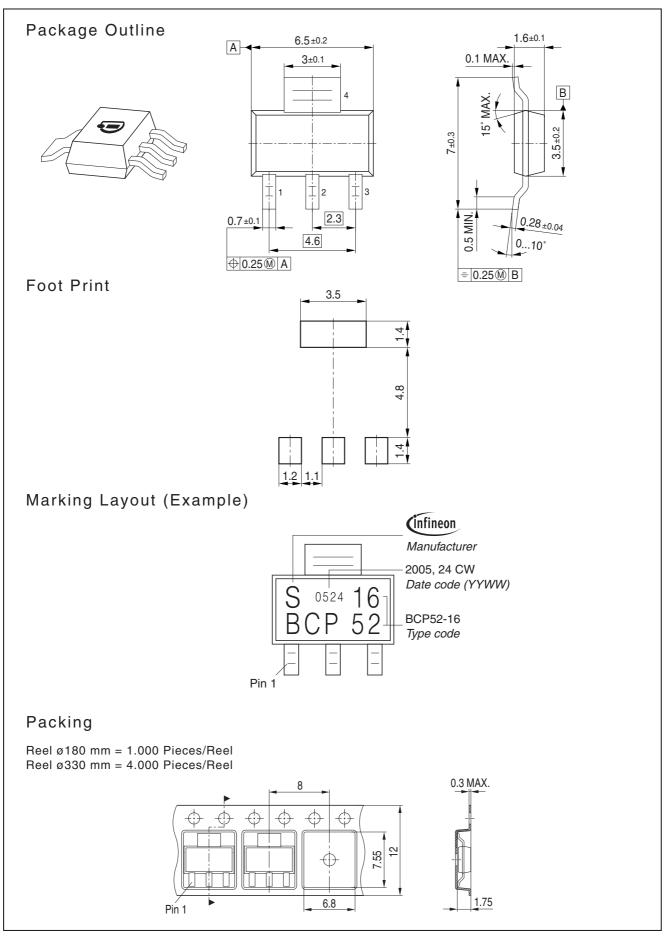
 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$



Total power dissipation $P_{tot} = f(T_S)$









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